

Features

- High reliability
- General purpose leads
- Peak wavelength λp=850nm
- Mechanically and spectrally matched to the phototransistor
- Low forward voltage
- High radiant intensity

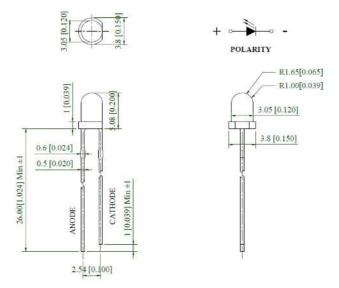
Applications

- Optoelectronic Switch
- IR Touch-Panel
- Industrial IR Equipment
- Consumer Electronics
- High Speed IR Communications

Description

- The infrared emitting diode (850nm) is a high intensity diode, molded in a water clear transparent plastic package.
- The device is spectrally matched with silicon photodiode and phototransistor.

Package Dimensions in mm



Notes:

- 1. All dimensions are in millimeters (inches).
- 2. Tolerance is \pm 0.25 mm (.010 η) unless otherwise noted.

Figure 1. INL-3AIR30 Package Dimensions



Absolute Maximum Rating at 25°C (Note 1)

Product	Emission Color	P _d (mW)	I _F (mA)	I _{FP} * (A)	V _R (V)	T _{OP} (°C)	T _{ST} (°C)
INL-3AIR30	Infrared	160	100	1	5	-40°C~+80°C	-40°C~+85°C

Notes

Electrical Characteristics $T_A = 25\%$ (Note 1)

	Emission	1 (V _F (V)		λ(nm)			Viewing Angle	Ee(mW/sr)		
	Product	Color	I _F (mA)	min	max	λ_{D}	$\lambda_{ extsf{P}}$	Δλ	2 0 1/2	min	typ.
	INL-3AIR30	Infrared	20	1.0	1.6	-	850	45	30	6	12

Notes

1. Performance guaranteed only under conditions listed in above tables.

ESD Precaution

ATTENTION: Electrostatic Discharge (ESD) protection



The symbol above denotes that ESD precaution is needed. ESD protection for GaP and AlGaAs based chips is necessary even though they are relatively safe in the presence of low static-electric discharge. Parts built with AllnGaP, GaN, or/and InGaN based chips are STATIC SENSITIVE devices. ESD precaution must be taken during design and assembly.

If manual work or processing is needed, please ensure the device is adequately protected from ESD during the process.

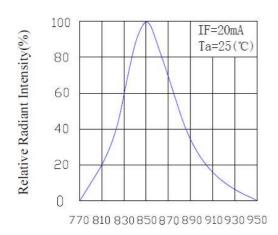
Please be advised that normal static precautions should be taken in the handling and assembly of this device to prevent damage or degradation which may be induced by electrostatic discharge (ESD).

^{1.} Condition for IFP is pulse of 1/10 duty and 1kHz frequency



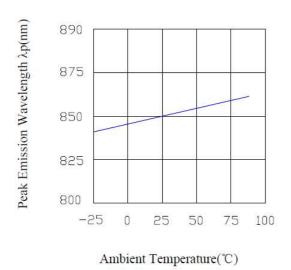
Typical Characteristic Curves

Spectral Distribution

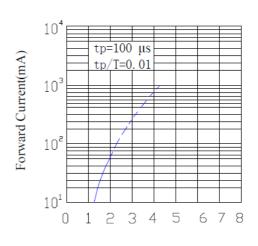


Wavelength λ(nm)

Peak Emission Wavelength & Ambient Temperature

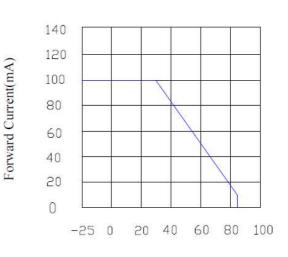


Forward Current & Forward Voltage



Forward Voltage(V)

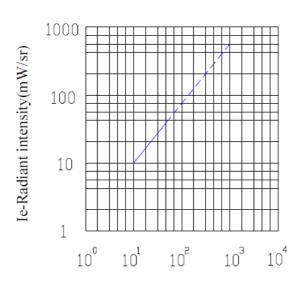
Forward Current & Ambient Temperature



Ambient Temperature(℃)

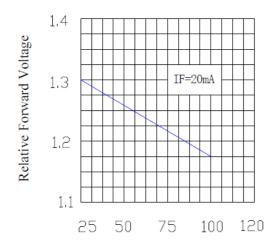


Relative Intensity & Forward Current



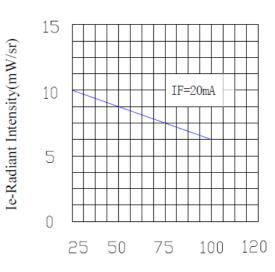
IF-Forward Current(mA)

Forward Voltage & Ambient Temperature(°C)



Ambient Temperature (°C)

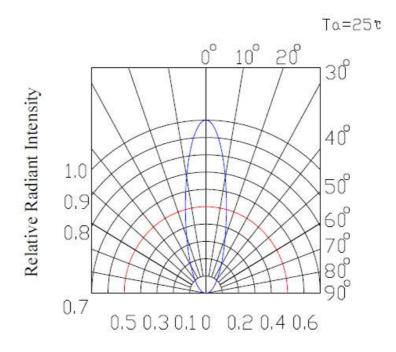
Relative Intensity & Ambient Temperature($^{\circ}$ C)



Ambient Temperature (°C)



Typical Characteristic Curves – Radiation Pattern

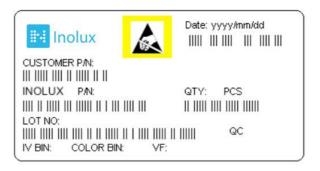


Ordering Information

Product	Emission Color	Technology	Test Current I _F (mA)	Radiant Intensity Ee (mW/sr) (Typ.)	Forward Voltage V _F (V) (Typ.)	Orderable Part Number
INL-3AIR30	Infrared	AlGaAs	20	12	1.4	INL-3AIR30



Label Specifications



Inolux P/N:

I	N	L	-	3	А	-	IR	3	0		Х	Х	Х	Х
				Package		Lens	Color	View Angle			Customized Stamp-off			
	Inolu mp T			stan	A = dard nm	(Blank) = clear	IR = 850nm	30 =	30 deg.					

Lot No.:

Z	2	0	1	7	01	24	001	
Internal		Voor (2017	2019 \	Month	Data	Corial		
Tracker		Year (2017)	, 2010,)	WIOTILIT	Date	Serial		





Reliability

Item Frequency/ lots/ samples failures		Standards Reference	Conditions		
Precondition	For all reliability monitoring tests according to JEDEC Level 2	J-STD-020	1.) Baking at 85°C for 24hrs 2.) Moisture storage at 85°C/60% R.H. for 168hrs		
Solderability	1Q/ 1/ 22/ 0	JESD22-B102-B And CNS-5068	Accelerated aging 155°C/ 24hrs Tinning speed: 2.5+0.5cm/s Tinning: A: 215°C/ 3+1s or B: 260°C/ 10+1s		
Resistance to soldering heat		CNS-5067	Dipping soldering terminal only Soldering bath temperature A: 260+/-5°C; 10+/-1s B: 350+/-10°C; 3+/-0.5s		
Operating life test	1Q/ 1/ 40/ 0	CNS-11829	1.) Precondition: 85°C baking for 24hrs 85°C/ 60%R.H. for 168hrs 2.) Tamb25°C; IF=20mA; duration 1000hrs		
High humidity, high temperature bias	1Q/ 1/ 45/ 0	JESD-A101-B	Tamb: 85°C Humidity: 85% R.H., IF=5mA Duration: 1000hrs		
High temperature bias	1Q/ 1/ 20	IN specs.	Tamb: 55°C IF=20mA Duration: 1000hrs		
Pulse life test	1Q/ 1/ 40/ 0		Tamb25°C, If=20mA,, Ip=100mA, Duty cycle=0.125 (tp=125 μ s,T=1sec) Duration 500hrs)		
Temperature cycle	1Q/ 1/ 76/ 0	JESD-A104-A IEC 68-2-14, Nb	A cycle: -40 degree C 15min; +85 degree C 15min Thermal steady within 5 min 300 cycles 2 chamber/ Air-to-air type		
High humidity storage test	1Q/ 1/ 40/ 0	CNS-6117	60+3°C 90+5/-10% R.H. for 500hrs		
High temperature storage test	1Q/ 1/ 40/ 0	CNS-554	100+10°C for 500hrs		
Low temperature storage test	1Q/ 1/ 40/ 0	CNS-6118	-40+5°C for 500hrs		





Revision History

Changes since last revision	Pa	age	Version No.	Revision Date
Initial Release			1.0	01-19-2019
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- 2. A critical component in any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.